

Title (en)
METHOD FOR PRODUCING A SILICONE FOIL, SILICONE FOIL AND OPTOELECTRONIC SEMICONDUCTOR COMPONENT COMPRISING A SILICONE FOIL

Title (de)
VERFAHREN ZUR HERSTELLUNG EINER SILIKONFOLIE, SILIKONFOLIE UND OPTOELEKTRONISCHES HALBLEITERBAUTEIL MIT EINER SILIKONFOLIE

Title (fr)
PROCÉDÉ DE FABRICATION D'UN FILM EN SILICONE, FILM EN SILICONE ET COMPOSANT SEMI-CONDUCTEUR OPTOÉLECTRONIQUE MUNI D'UN FILM EN SILICONE

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Application
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Abstract (en)
[origin: WO2012045511A2] In at least one embodiment of the method, the latter serves for producing a silicone foil (2) by means of molding for use in an optoelectronic semiconductor component (10). The method comprises the following steps: introducing a mold foil (1) into a mold (5), introducing a carrier foil (3) into the mold (5), wherein the carrier foil (3) is fitted on a substrate foil (4) and the substrate foil (4) projects laterally beyond the carrier foil (3), providing and applying a silicone base composition (20) to the mold foil (1) or to the carrier foil (3), molding the silicone base composition (20) to form the silicone foil (2) between the mold foil (1) and the carrier foil (3), wherein the silicone base composition is brought into contact with the substrate foil (4) in an overlap region (24) laterally alongside the carrier foil (3), removing the mold foil (1) from the silicone foil (2), and separating the overlap region (24).

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